

# Schottky Barrier Diode

## RB481K

### ● Applications

Low current rectification

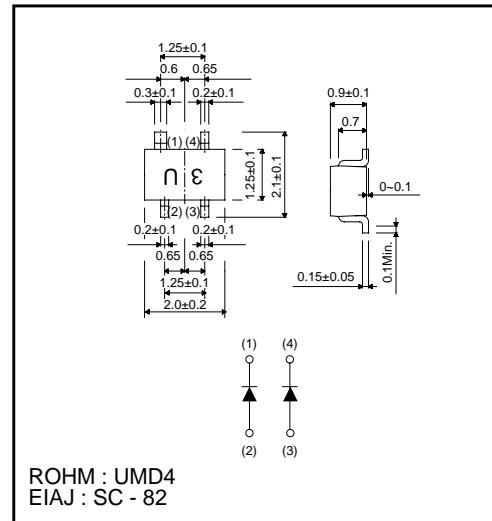
### ● Features

- 1) Compact size.
- 2) High reliability.
- 3) Extremely low forward voltage.
- 4) This is a composite component and is ideal for reducing the number of components used.

### ● Construction

Silicon epitaxial planar

### ● External dimensions (Units: mm)



### ● Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	30	V
DC reverse voltage	$V_R$	30	V
Mean rectifying current	$I_o$	0.2	A
Peak forward surge current*	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40~+125	$^\circ\text{C}$

\* 60 Hz for 1  $\text{mA}$

### ● Electrical characteristics ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{F1}$	—	0.18	0.28	V	$I_F=1\text{mA}$
	$V_{F2}$	—	0.25	0.33	V	$I_F=10\text{mA}$
	$V_{F3}$	—	0.34	0.43	V	$I_F=100\text{mA}$
	$V_{F4}$	—	0.40	0.50	V	$I_F=200\text{mA}$
Reverse current	$I_R$	—	3.6	30	$\mu\text{A}$	$V_R=10\text{V}$

## Diodes

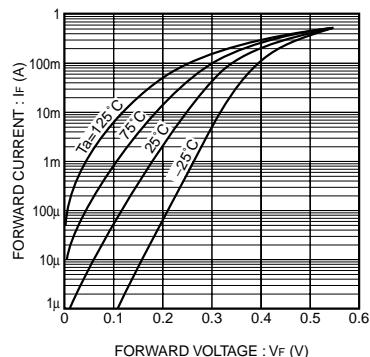
● Electrical characteristic curves ( $T_a=25^\circ\text{C}$ )

Fig. 1 Forward temperature characteristic

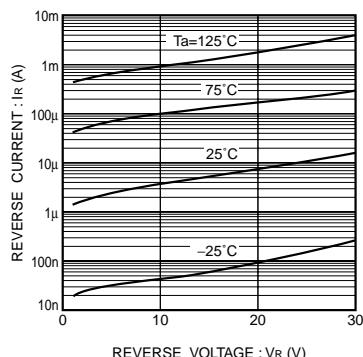


Fig. 2 Reverse temperature characteristic

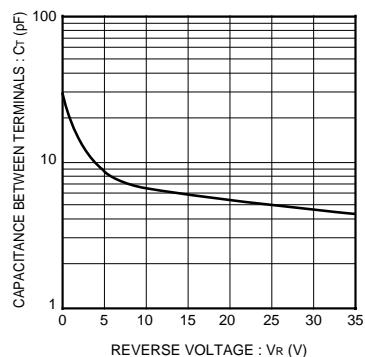


Fig. 3 Capacitance between terminals characteristic